

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±20	V
	T _A = +25°C	I _D	16	A
Continuous Drain Current, V _{GS} = 10V (Note 6)	T _A = +70°C		13	
	T _C = +25°C	· I _D	45	А
	T _C = +70°C		35	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	80	Α	
Maximum Continuous Body Diode Forward Current (Note 6)		Is	20	Α
Avalanche Current, L = 0.1mH		I _{AS}	33	Α
Avalanche Energy, L = 0.1mH		E _{AS}	55	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	Pn	0.9	W	
	T _A = +70°C	T PD	0.6	VV	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	137	°C/W		
Total Power Dissipation (Note 6)	T _A = +25°C	D-	2.1	W	
	T _A = +70°C	P _D	1.4	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	59	°C/W	
Thermal Resistance, Junction to Case (Note 6)		R ₀ JC	7.8	°C/W	
Operating and Storage Temperature Range		$T_{J,} T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 24V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 7)						•	
Gate Threshold Voltage	V _{GS(th)}	1	1.4	2.5	V	V _{DS} = V _{GS} , I _D = 250μA	
Static Drain-Source On-Resistance		_	4.0	5.5	mΩ	V _{GS} = 10V, I _D = 20A	
	R _{DS(on)}	_	4.9	9		V _{GS} = 4.5V, I _D = 16A	
Diode Forward Voltage	V_{SD}	_	0.68	1	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	2,000	_	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	315	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	248	_	pF		
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	20	_	nC	V _{DS} = 15V, I _D = 15A	
Total Gate Charge (V _{GS} = 10V)	Qg	_	42	_	nC		
Gate-Source Charge	Q _{gs}	_	4.7	_	nC		
Gate-Drain Charge	Q_{gd}	_	7.4	_	nC		
Turn-On Delay Time	t _{D(on)}	_	3.9	_	ns	V_{DD} = 15V, V_{GS} = 10V, R_G = 3.3 Ω , I_D = 15A	
Turn-On Rise Time	t _R	_	4.1	_	ns		
Turn-Off Delay Time	$t_{D(off)}$	_	31	_	ns		
Turn-Off Fall Time	t _F	_	14.6	_	ns		
Reverse Recovery Time	t _{RR}	_	15	_	ns	I _F = 15A, di/dt = 100A/μs	
Reverse Recovery Charge	Q_{RR}	_	6	_	nC		

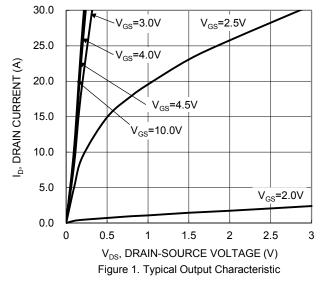
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to production testing.





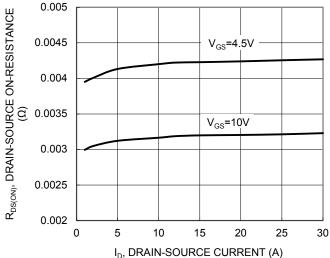


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

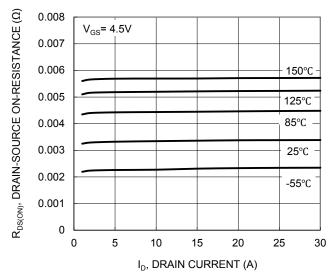


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

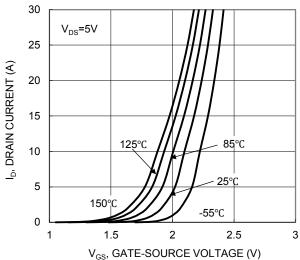


Figure 2. Typical Transfer Characteristic

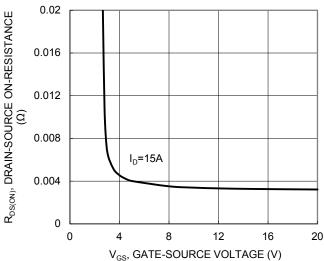


Figure 4. Typical Transfer Characteristic

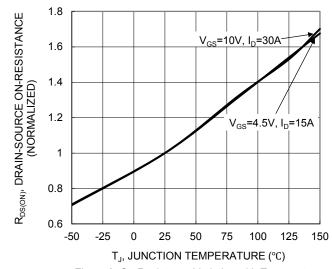


Figure 6. On-Resistance Variation with Temperature



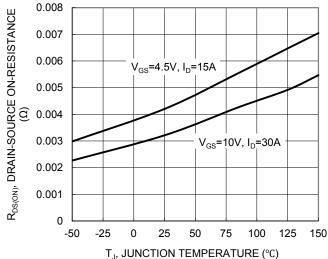


Figure 7. On-Resistance Variation with Temperature

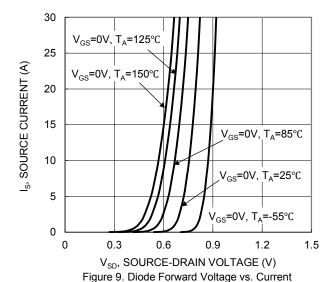


Figure 11. Typical Junction Capacitance

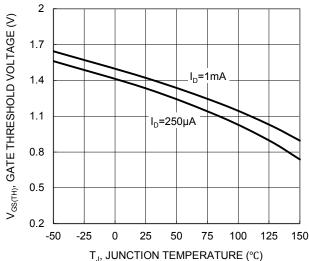


Figure 8. Gate Threshold Variation vs. Junction Temperature

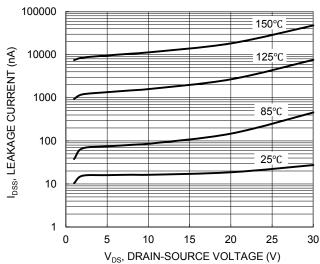


Figure 10. Typical Drain-Source Leakage Current vs.

Voltage

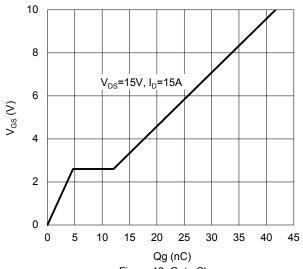
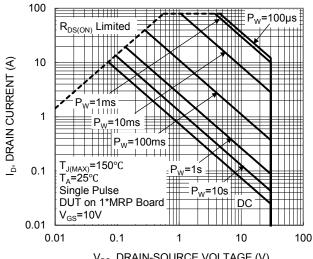


Figure 12. Gate Charge

10000

f=1MHz





 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 13. SOA, Safe Operation Area

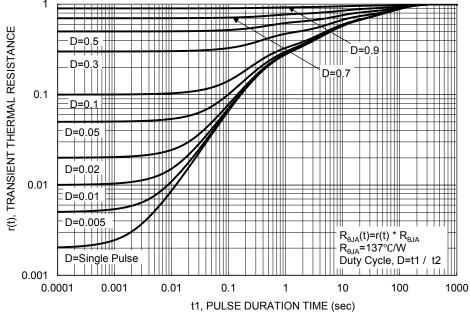


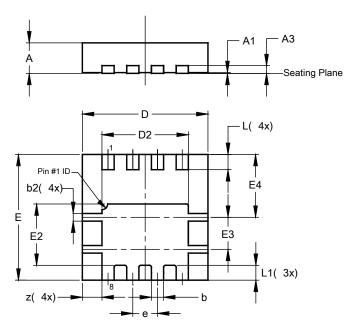
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

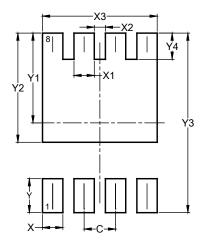


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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